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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **DEL PUPPO, Hélène** [FR/US]; 4312 Grover Drive, Fremont, CA 94536 (US). **LIN, Frank** [US/US]; 43254 Livermore Common Hill Drive, Fremont, CA 94539 (US). **LEE, Chris** [US/US]; 6848 Aitken Drive, Oakland, CA 94611 (US). **VAHEDI, Vahid** [US/US]; 1503 Posen Avenue, Albany, CA 94706 (US). **KAMP, Thomas, A.** [US/US]; 1693 Golden Tree Drive, San Jose, CA 95131 (US). **MILLER, Alan, J.** [US/US]; 265 Corliss Drive, Morgan Hill, 94556 (US).

(74) Agent: **GENCARELLA, Michael, L.**; Martine & Penilla, LLP, 710 Lakeway Drive, Suite 170, Sunnyvale, CA 94085 (US).

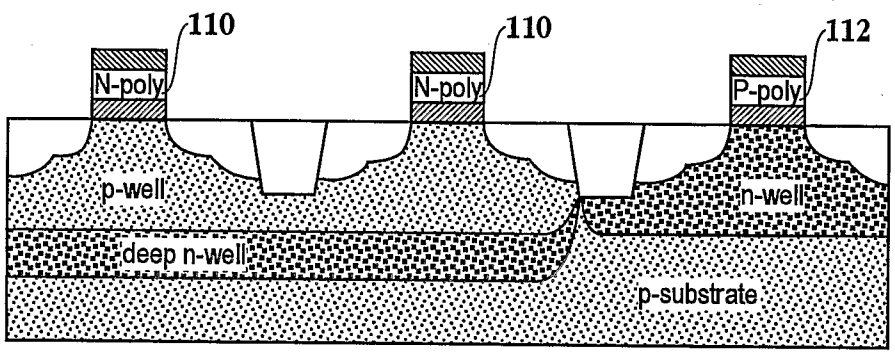
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(54) Title: METHOD TO IMPROVE PROFILE CONTROL AND N/P LOADING IN DUAL DOPED GATE APPLICATIONS



(57) Abstract: A method for etching a polysilicon gate structure in a plasma etch chamber is provided. The method initiates with defining a pattern protecting a polysilicon film to be etched. Then, a plasma is generated. Next, substantially all of the polysilicon film that is unprotected is etched. Then, a silicon containing gas is introduced and a remainder of the polysilicon film is etched while introducing a silicon containing gas. An etch chamber configured to introduce a silicon containing gas during an etch process is also provided.

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